

ABSTRACT OF THE DISCLOSURE

5 The semiconductor device according to the present
invention comprises a V-groove having V-shaped cross-
section formed on a semiconductor substrate or on an
10 epitaxial growth layer grown on a semiconductor substrate,
and an active layer is provided only at the bottom of said
V-groove. The method for manufacturing a semiconductor
device according to the present invention comprises the
steps of forming a stripe-like etching protective film in
15 <011> direction of a semiconductor substrate or an epitaxial
growth layer grown on it, performing gas etching using
hydrogen chloride as etching gas on a semiconductor
substrate or on an epitaxial growth layer grown on a
semiconductor substrate to form a V-groove, and forming an
active layer at the bottom of said V-groove.